

## SKiiP 342 GD 120 - 314 CTV

| Absolute Maximum Ratings        |   | Values             | Units             |
|---------------------------------|---|--------------------|-------------------|
| Symbol                          | Conditions <sup>1)</sup>                              |                    |                   |
| IGBT & Inverse Diode            |   |                    |                   |
| V <sub>CES</sub>                |   | 1200               | V                 |
| V <sub>CC</sub> <sup>9)</sup>   | Operating DC link voltage                             | 900                | V                 |
| I <sub>C</sub>                  | T <sub>heatsink</sub> = 25 °C                         | 300                | A                 |
| T <sub>j</sub> <sup>3)</sup>    | IGBT & Diode  | - 40 ... + 150     | °C                |
| V <sub>isol</sub> <sup>4)</sup> | AC, 1 min.  | 3000 <sup>5)</sup> | V                 |
| I <sub>F</sub>                  | T <sub>heatsink</sub> = 25 °C                         | 300                | A                 |
| I <sub>FM</sub>                 | T <sub>heatsink</sub> = 25 °C; t <sub>p</sub> < 1 ms  | 600                | A                 |
| I <sub>FSM</sub>                | t <sub>p</sub> = 10 ms; sin.; T <sub>j</sub> = 150 °C | 2160               | A                 |
| I <sup>2</sup> t (Diode)        | t <sub>p</sub> = 10 ms; T <sub>j</sub> = 150 °C       | 23,4               | kA <sup>2</sup> s |

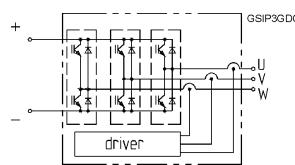
SKiiPPACK®  
SK integrated  
intelligent Power PACK

3-phase bridge

SKiiP 342 GD 120  
+ Driver 314 CTV <sup>7,13)</sup>

Preliminary Data

Case S3



## Characteristics

| Symbol                             | Conditions <sup>1)</sup>  | min.               | typ.       | max. | Units |
|------------------------------------|---|--------------------|------------|------|-------|
| V <sub>(BR)CES</sub>               | Driver without power supply   | ≥ V <sub>CES</sub> | —          | —    | V     |
| I <sub>CES</sub>                   | V <sub>GE</sub> = 0 { T <sub>j</sub> = 25 °C } V <sub>CE</sub> = V <sub>CES</sub> { T <sub>j</sub> = 125 °C } | —                  | 0,3        | —    | mA    |
| V <sub>CEsat</sub>                 | I <sub>C</sub> = 225 A { T <sub>j</sub> = 25 (125) °C }   | —                  | 2,6(3)     | —    | V     |
| V <sub>CEsat</sub>                 | I <sub>C</sub> = 300 A { T <sub>j</sub> = 25 (125) °C }   | —                  | 3,0(3,6)   | —    | V     |
| C <sub>CHC</sub>                   | per SKiiPPACK AC side   | —                  | 0,8        | —    | nF    |
| L <sub>CE</sub>                    | Top (Bottom)  | —                  | 15         | —    | nH    |
| t <sub>d(on)</sub>                 | I <sub>C</sub> = 300 A<br>T <sub>j</sub> = 125 °C<br>inductive load   | —                  | 150        | —    | ns    |
| t <sub>d(on)Driver</sub>           |   | —                  | 1,0        | —    | μs    |
| t <sub>r</sub>                     |   | —                  | 100        | —    | ns    |
| t <sub>d(off)</sub>                |   | —                  | 0,6        | —    | μs    |
| t <sub>d(off)Driver</sub>          |   | —                  | 1,0        | —    | μs    |
| t <sub>f</sub>                     |   | —                  | 80         | —    | ns    |
| E <sub>on</sub> + E <sub>off</sub> | V <sub>CC</sub> = 600 V / 900 V   | —                  | 90 / 147   | —    | mJ    |
| Inverse Diode <sup>2)</sup>        |   |                    |            |      |       |
| V <sub>F</sub> = V <sub>EC</sub>   | I <sub>F</sub> = 225 A { T <sub>j</sub> = 25 (125) °C }   | —                  | 1,9(1,8)   | —    | V     |
|                                    | I <sub>F</sub> = 300 A { T <sub>j</sub> = 25 (125) °C }   | —                  | 2,1(2,05)  | —    | V     |
| E <sub>on</sub> + E <sub>off</sub> | I <sub>F</sub> = 300 A; T <sub>j</sub> = 125 °C   | —                  | 12         | —    | mJ    |
| IGBT / Inverse Diode <sup>2)</sup> |   |                    |            |      |       |
| V <sub>TO</sub>                    | T <sub>j</sub> = 125 °C   | —                  | 1,38 / 0,9 | —    | V     |
| r <sub>T</sub>                     | T <sub>j</sub> = 125 °C   | —                  | 7,4 / 3,8  | —    | mΩ    |
| Thermal Characteristics            |   |                    |            |      |       |
| R <sub>thjh</sub>                  | per IGBT  | —                  | 0,09       | —    | K/W   |
| R <sub>thjh</sub>                  | per diode   | —                  | 0,23       | —    | K/W   |
| T <sub>tp</sub> <sup>12)</sup>     | Over temperature protection   | 110                | 115        | 120  | °C    |
| R <sub>thha</sub> <sup>6)</sup>    | P16/280 F; v <sub>air</sub> = 285 m <sup>3</sup> / h  | —                  | 0,036      | —    | K/W   |
| SKiiPPACK protection               |   |                    |            |      |       |
| I <sub>TRIPSC</sub>                | Short circuit protection  | 367                | 375        | 383  | A     |
| I <sub>TRIPLG</sub>                | Ground fault protection   | —                  | 90         | —    | A     |
| T <sub>TRIP</sub>                  | Overtemperature protection  | 110                | 115        | 120  | °C    |
| U <sub>DCTRIP</sub> <sup>13)</sup> | U <sub>DC</sub> -protection   | 900                | 920        | 940  | V     |
| Mechanical Data                    |   |                    |            |      |       |
| Mdc                                | for DC terminals, SI Units  | 4                  | —          | 6    | Nm    |
| Mac                                | for AC terminals, SI Units  | 8                  | —          | 10   | Nm    |
| Case                               |   |                    | S3         |      |       |

## Features

- Low thermal impedance
- Optimal thermal management with integrated heatsink
- Pressure contact technology with increased power cycling capability, compact design
- Low stray inductance
- High power, small losses
- Overtemp. protection
- Short circuit protection, due to evaluation of current sensor signals
- Isolated power supply

1) T<sub>heatsink</sub> = 25 °C, unless otherwise specified

2) CAL = Controlled Axial Lifetime Technology (soft and fast)

3) without driver

4) Driver input to DC link/AC output or DC link/AC output to heatsink

5) 4 kV (AC; on request)

6) other heatsink on request

7) C - integrated current sensors

T - Temperature protection

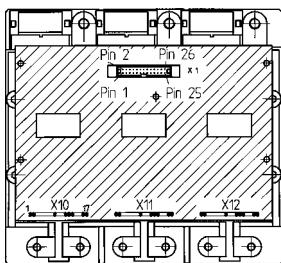
V - 15 V or 24 V power supply

9) with SK-DC link (low inductance)

12) thermal reference for R<sub>thjh</sub>; R<sub>thha</sub>  
13) option available for driver

U - DC-link voltage sense

**SKiiPPACK®**  
**SK integrated**  
**intelligent Power PACK**  
**3-phase bridge**  
**SKiiP 342 GD 120**  
**+ Driver 314 CTV<sup>3,5)</sup>**  
Preliminary Driver Data



#### Features

- CMOS compatible inputs
- Short circuit protection by evaluation of current sensor signals
- Drive interlock top/bottom
- Isolation by transformers
- Supply undervoltage protection
- Overttemperature protection
- Udc-monitoring (option)

- 1) 24 V - power supply
- 2) Open collector output, external pull-up resistor necessary
- 3) C - integrated current sensors
- T - Temperature protection
- V - 15 V or 24 V power supply
- 4) 4 kVAC (on request)
- 5) option available for driver
- U - DC-link voltage sense
- 6) IAC - AC-current per phase

**SKiiP 342 GD 120 - 314 CTV**  
**Driver for 3-phase bridge**

| <b>Absolute Maximum Ratings</b>    |   | <b>Values</b> | <b>Units</b> | <b>remark</b> |
|------------------------------------|---|---------------|--------------|---------------|
| <b>Symbol</b>                      | <b>Conditions</b>   |               |              |               |
| V <sub>S1</sub>                    | supply voltage primary  | 18            | V            | pin 16 / 17   |
| V <sub>S2</sub> <sup>1)</sup>      | supply voltage primary  | 30            | V            | pin 14 / 15   |
| I <sub>outmax</sub>                | output peak current max.  | ± 10          | A            |               |
| I <sub>outAV</sub>                 | output average current  | ± 50          | mA           |               |
| f <sub>swmax</sub>                 | switching frequency max.  | 20            | kHz          |               |
| dV/dt                              | rate of rise and fall of voltage<br>(secondary to primary side) | 75            | kV/μs        |               |
| V <sub>isol IO</sub> <sup>4)</sup> | Isol. test volt. IN/OUT<br>(RMS; 1 min)                         | 3             | kV~          |               |
| V <sub>isol 12</sub>               | Isol. test volt. output 1 -<br>output 2                         | 1,5           | kV=          |               |
| T <sub>op</sub> , T <sub>stg</sub> | operating / stor. temperature                                   | - 25 ... + 85 | °C           |               |

| <b>Characteristics (Ta = 25 °C)</b> |   | <b>Values</b>  | <b>Units</b> | <b>remark</b>                    |
|-------------------------------------|---|--|--------------|----------------------------------|
| <b>Symbol</b>                       | <b>Conditions</b>                                   |  |              |                                  |
| V <sub>S1</sub> <sup>1)</sup>       | supply voltage primary                              | 15,0 ± 4 %   | V            | pin 16 / 17                      |
| V <sub>S2</sub>                     | supply voltage primary                              | 24,0   | V            | pin 14 / 15                      |
|                                     |   | +25%/-15%  |              |                                  |
| V <sub>UVs</sub>                    | supply voltage monitoring                           | 13,5 / 19,5  | V            | 15 V / 24 V                      |
| I <sub>S01</sub>                    | sup.current pr.side (standby)                       | 340  | mA           | 15 V supply                      |
| I <sub>S02</sub> <sup>1)</sup>      | sup.current pr.side (standby)                       | 250  | mA           | 24 V supply                      |
| I <sub>S1</sub>                     | sup. current pr.side (max)<br>at f <sub>swmax</sub> | 860 +<br>3 · I <sub>AC</sub> <sup>6)</sup>                 | mA           | 15 V supply                      |
| I <sub>S2</sub> <sup>1)</sup>       | sup. current pr.side (max)<br>at f <sub>swmax</sub> | 1000<br>630 +<br>3 · I <sub>AC</sub> <sup>6)</sup><br>1350 | mA           | 24 V supply                      |
| V <sub>IT+</sub>                    | input thresh. volt. (high) min                      | 11,2   | V            |                                  |
| V <sub>IT-</sub>                    | input thresh. volt. (low) max.                      | 5,4  | V            |                                  |
| V <sub>GE(on)</sub>                 | turn-on output gate voltage                         | 15   | V            |                                  |
| V <sub>GE(off)</sub>                | turn-off output gate voltage                        | - 7  | V            |                                  |
| t <sub>d(on)</sub>                  | propagation delay time on                           | 1,0  | μs           | typ.                             |
| t <sub>d(off)</sub>                 | propagation delay time off                          | 1,0  | μs           | typ.                             |
| t <sub>TD</sub>                     | dead time of interlock                              | 2,2  | μs           | typ.                             |
| V <sub>OL</sub> <sup>2)</sup>       | logic low output voltage                            | < 600  | mV           | 15 mA                            |
| V <sub>OH</sub> <sup>2)</sup>       | logic high output voltage                           | max. 30  | V            |                                  |
| t <sub>pd(on-error)</sub>           | propag. delay time-on error                         | 1  | μs           |                                  |
| t <sub>p RESET</sub>                | min. pulse width error<br>memory RESET              | 8  | μs           |                                  |
| T <sub>TRIP</sub>                   | max. temperature                                    | 115 ± 5  | °C           |                                  |
| I <sub>AOmax</sub>                  | max. output current                                 | ± 5  | mA           | pin<br>13/20/22/24/26            |
| U <sub>TRIPSC</sub>                 | overcurrent trip level                              | 10   | V            | 10 V=125% I <sub>c</sub>         |
| U <sub>DCTRIP</sub>                 | overvoltage trip level                              | 9  | V            | 9 V = 900 V;<br>using option "U" |